TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2574FK

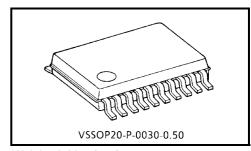
Low-Voltage Octal D-Type Flip-Flop with 3.6 V Tolerant Inputs and Outputs

The TC7MA2574FK is a high performance CMOS octal D-type flip-flop. Designed for use in 1.8 V, $2.5~\rm V$ or $3.3~\rm V$ systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to $3.6\ V$.

This 8 bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (\overline{OE}). When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The $26\,\Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.



Weight: 0.03 g (typ.)

All inputs are equipped with protection circuits against static discharge.

Features

- 26Ω series resistors on outputs.
- Low voltage operation: $VCC = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 5.1 \text{ ns (max) (V}_{CC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 6.2 \text{ ns (max) (V}_{CC} = 2.3 \sim 2.7 \text{ V})$

 $t_{pd} = 9.8 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $IOH/IOL = \pm 4 \text{ mA (min) (VCC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model $> \pm 2000 \text{ V}$

- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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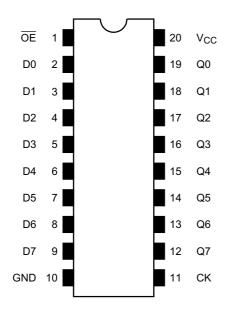
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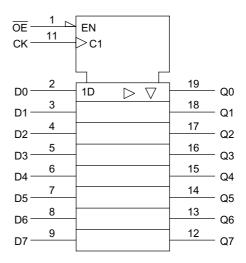
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Pin Assignment (top view)



IEC Logic Level



Truth Table

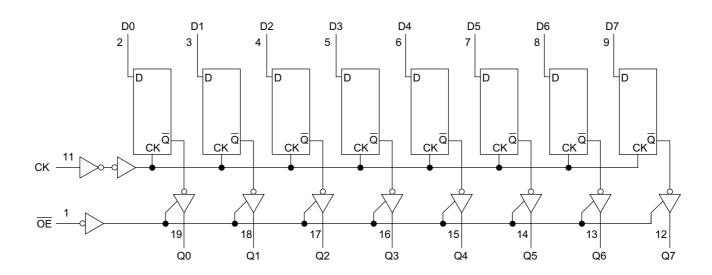
	Inputs					
ŌĒ	CK	D	Outputs			
Н	Х	Х	Z			
L	\rightarrow	Х	Q _n			
L		L	L			
L		Н	Н			

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~4.6	V
DC input voltage	V _{IN}	-0.5~4.6	٧
DC output voltage	Va .	-0.5~4.6 (Note1)	٧
DC output voltage	Vout	-0.5~V _{CC} + 0.5 (Note2)	V
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note3)	mA
DC output current	Гоит	±50	mA
Power dissipation	PD	180	mW
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65~150	°C

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit	
Supply voltage	\/	1.8~3.6	V	
Supply voltage	V _{CC}	1.2~3.6 (Note4)	V	
Input voltage	V _{IN}	-0.3~3.6	V	
Output voltage	\/	0~3.6 (Note5)	V	
Output voltage	Vout	0~V _{CC} (Note6)	v	
		±12 (Note7)		
Output current	I _{OH} /I _{OL}	±8 (Note8)	mA	
		±4 (Note 9)		
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V	

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: $V_{CC} = 3.0 \sim 3.6 \text{ V}$ Note8: $V_{CC} = 2.3 \sim 2.7 \text{ V}$

Note9: V_{CC} = 1.8 V

Note10: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$



Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Character	stics	Symbol	Test	Condition	V _{CC} (V)	Min	Max	Unit
Innut valtage	High level	V _{IH}		_	2.7~3.6	2.0	_	V
Input voltage	Low level	V _{IL}		_	2.7~3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7~3.6	V _{CC} - 0.2		
	High level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -6 mA	2.7	2.2	_	
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_	
Output voltage				I _{OH} = -12 mA	3.0	2.2	_	V
		evel Vol	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.7~3.6	_	0.2	
	Low level			I _{OL} = 6 mA	2.7	_	0.4	
	Low level	VOL		$I_{OL} = 8 \text{ mA}$	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8	
Input leakage curre	ent	I _{IN}	V _{IN} = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
3-state output off-si	tate current	l _{OZ}	$V_{IN} = V_{IH}$ or V_{IL}		2.7~3.6		±10.0	
3-state output on-s	3-state output off-state current		V _{OUT} = 0~3.6 V		2.7~3.0		±10.0	μΑ
Power off leakage	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
		loo	V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply c	Quiescent supply current	Icc	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7~3.6	_	±20.0	μΑ
		Δl _{CC}	$V_{IH} = V_{CC} - 0.6 V$ (per	input)	2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Innut voltage	High level	V _{IH}		_	2.3~2.7	1.6	_	V
Input voltage	Low level	V _{IL}		_	2.3~2.7		0.7	V
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_	
	High level	V _{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -4 \text{ mA}$	2.3	2.0	_	
Output voltage			.	$I_{OH} = -6 \text{ mA}$	2.3	1.8	_	V
				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_	
			$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	2.3~2.7	_	0.2	
	Low level	V_{OL}		I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3	_	0.6	
Input leakage curr	ent	I _{IN}	V _{IN} = 0~3.6 V	•	2.3~2.7	_	±5.0	μΑ
2 state sutput off	atata aumant	1	$V_{IN} = V_{IH}$ or V_{IL}		2.3~2.7	7	.40.0	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.3~2.1		±10.0	μΑ
Power off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Outro and according to the second		laa	V _{IN} = V _{CC} or GND		2.3~2.7	_	20.0	μА
Quiescent supply	Current	Icc	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3~2.7	_	±20.0	μΑ



DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
lanut voltogo	High level	VIH		_	1.8~2.3	0.7× V _{CC}	_	V
Input voltage	Low level	V _{IL}		_	1.8~2.3		0.2× V _{CC}	٧
	High level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu A$	1.8	V _{CC} - 0.2		V
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	
	Low level	V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu A$	1.8	_	0.2	
				I _{OL} = 4 mA	1.8	_	0.3	
Input leakage curre	nt	I _{IN}	V _{IN} = 0~3.6 V		1.8	_	±5.0	μΑ
3-state output off-state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μΑ
Power off leakage of	current	I _{OFF}	V _{IN} , V _{OUT} = 0~3.6 V		0	_	10.0	μΑ
Quiescent supply co	0		$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	^
Quiescent supply co	an c nt	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.$	6 V	1.8	—	±20.0	μΑ



AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500~\Omega$)

Characteristics	Symbol	Symbol Test Condition		Min		Unit
Characteristics	Symbol	rest condition	V _{CC} (V)	IVIIII	Max	Oi ii
			1.8	100	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
	4		1.8	1.5	9.8	
Propagation delay time (CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.2	ns
	t _{pHL}		3.3 ± 0.3	0.6	5.1	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	0.8	6.5	ns
	t _{pZH}		3.3 ± 0.3	0.6	5.0	
		Figure 1, Figure 3	1.8	1.5	7.7	ns
3-state output disable time	t _{pLZ}		2.5 ± 0.2	0.8	4.3	
	t _{pHZ}		3.3 ± 0.3	0.6	3.9	
	4	Figure 1, Figure 2	1.8	4.0	_	ns
Minimum pulse width (CK)	t _{w (H)}		2.5 ± 0.2	1.5	_	
	t _{w (L)}		3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0		ns
			3.3 ± 0.3	1.0		
	4		1.8	_	0.5	ns
Output to output skew	t _{osLH}	(Note11)	2.5 ± 0.2	_	0.5	
	t _{osHL}		3.3 ± 0.3	_	0.5	

For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$



Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 1.8	0.15	
Quiet output maximum dynamic V _{OL}	V_{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 3.3	0.35	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 1.8	-0.15	
Quiet output minimum dynamic $V_{\mbox{OL}}$		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 2.5	-0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 1.8	1.55	
Quiet output minimum dynamic V _{OH}	V_{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 3.3	2.65	

Note12: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Cymbol			V _{CC} (V)	ιyp.	Offic
Input capacitance	C _{IN}	_		1.8, 2.5, 3.3	6	pF
Output capacitance	C _{OUT}	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ (I	Note13)	1.8, 2.5, 3.3	20	pF

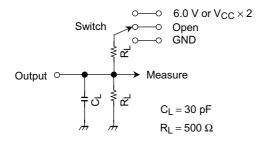
Note13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$



AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	6.0 V @V _{CC} = 3.3 ± 0.3 V V _{CC} × 2 @V _{CC} = 2.5 ± 0.2 V @V _{CC} = 1.8 V		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

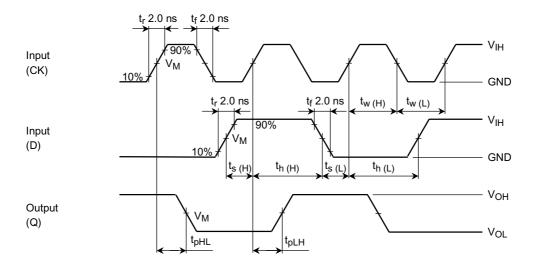


Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

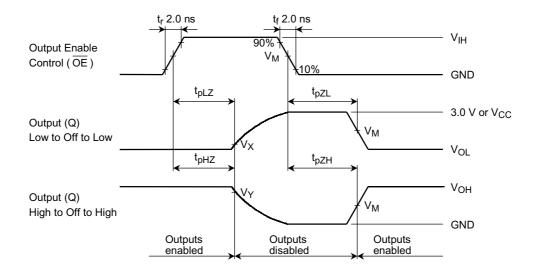
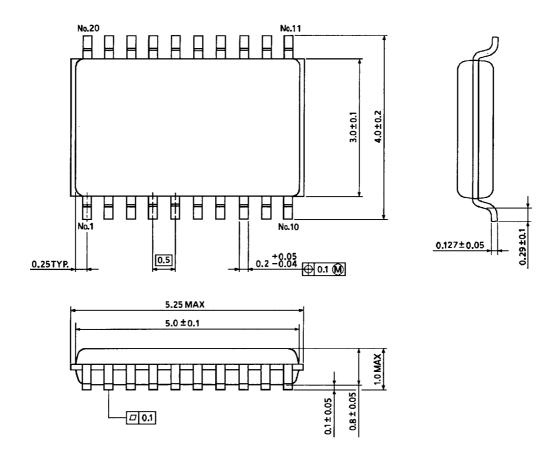


Figure 3 $t_{pLZ},\,t_{pHZ},\,t_{pZL},\,t_{pZH}$

Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

Package Dimensions



Weight: 0.03 g (typ.)